

Express Mail No. EV 148299860 US
Docket No. 2022927-7035362001

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Charles E. Hamilton, et al.	Assignee:	Aculight Corporation
Filing Date:	HEREWITH	Examiner:	Unknown
Serial No.:	NEW APPLICATION	Group Art Unit:	Unknown
Title:	SPECTRAL BEAM COMBINATION OF BROAD-STRIPE LASER DIODES		

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with 37 C.F.R. § 1.56, the references listed on the attached Form PTO-1449 are being brought to the attention of the Examiner for consideration in connection with the examination of the above-identified patent application.

I. Timing of the Information Disclosure Statement:

This Information Disclosure Statement is filed:

- ☒ With the new patent application submitted herewith (37 C.F.R. § 1.97(a)).
- ☐ Within three months after the filing date of the application or within three months after the date of entry of the national stage of a PCT application as set forth in 37 C.F.R. § 1.491.
- ☐ Before the mailing date of a first Office action on the merits. In the event, however, that an Office Action on the merits has crossed in the mail with this Information Disclosure Statement, no fee will be due if the certification below is checked. Otherwise, the Commissioner is hereby authorized to charge Deposit Account No. 50-2518 for the fee (\$180) set forth in 37 C.F.R. § 1.17(p) and any additional required fees.

This Information Disclosure Statement is filed:

- ☐ After the first Office Action and more than three months after the application's filing date; or PCT national stage date of entry filing but, as far as is known to the undersigned, prior to the mailing date of either a final rejection or a notice of allowance, whichever occurs first, and the Commissioner is hereby authorized to charge Deposit Account No. 50-2518 for the fee (\$180) set forth in 37 C.F.R. § 1.17(p) and any additional required fees.

This Information Disclosure Statement is filed:

- ☐ After the mailing date of either a final rejection or a notice of allowance, whichever occurred first, and is accompanied by the fee (\$180.00) set forth in 37 C.F.R. § 1.17(i)(1) and a certification as specified in 37 C.F.R. § 1.97(e), as checked below. This document is to be considered as a petition requesting consideration of the Information Disclosure Statement.

The undersigned certifies that:

- ☐ Each item of information contained in the Information Disclosure Statement was cited in a communication mailed from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this information disclosure statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication mailed from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned after making reasonable inquiry, was known to any individual designated in 37 C.F.R. § 1.56(c) more than three months prior to the filing of this Information Disclosure Statement.

II. Copies of the Cited Items:

- ☒ Copies of all of the items listed on the attached Form PTO-1449 are enclosed.
- ☐ Copies of only the following items listed on the attached Form PTO-1449 are enclosed: _____.
- ☐ Copies of those items which are marked with an asterisk (*) in the attached Form PTO-1499 are not supplied because they were previously cited by or submitted to the Patent Office in a prior Application No. _____, filed _____ and relied upon in this application for an earlier filing date under 35 U.S.C § 120. See 37 C.F.R. § 1.98(d).
- ☐ Copies of those items which are marked with an asterisk (**) in the attached Form PTO-1499 were cited in a foreign examination report in a related case. A copy of the search report and the cited references not already of record in this application are attached hereto.

III. Concise Explanation of Relevance:

- ☒ A concise explanation of relevance of the items listed on Form PTO-1449 is not given.
- ☐ A concise explanation of relevance of the items listed on Form PTO-1449 is in the form of an English language copy of a Search Report from a foreign patent office, issued in a counterpart application, which refers to the relevant portions of the references (copy attached).

IV. Conclusion:

Citation of the above documents shall not be construed as:

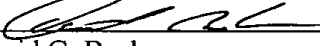
1. an admission that the documents are necessarily prior art with respect to the instant invention;
2. a representation that a search has been made, other than as described above; or
3. an admission that the information cited herein is, or is considered to be, material to patentability as defined in § 1.56(b).

It is respectfully requested that the Examiner indicate consideration of the cited references by returning a copy of the attached form PTO 1449 with initials or other appropriate marks.

The Commissioner is hereby authorized to charge Deposit Account No. 50-2518 Docket No. 2022927-7035362001 for any additional fees required in connection with the filing of this Information Disclosure Statement.

DATE: 10/16/03

Respectfully submitted,

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FORM PTO-1449 (Modified [6-1]) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT(S)' INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO.: 2022027-7035362001	SERIAL NO.: NEW APPLICATION
	INVENTOR(s): Charles E. Hamilton, et al.	
	FILING DATE: HEREWITH	GROUP ART UNIT: UNKNOWN

REFERENCE DESIGNATION		U.S. PATENT DOCUMENTS					
EXAM'R INITIAL		DOCUMENT NUMBER	DATE	NAME	Class	Subclass	Filing Date If Appropriate
	A1	6,192,062	01/20/01	Sanchez-Rubio, et al.	372	92	02/04/00

OTHER ART (Include Author, Title, Date, Pertinent Pages, etc.)

	C1	Ming-Wei Pan, et al., "Fiber-coupled high-power external-cavity semiconductor lasers for real-time Raman sensing", Applied Optics, Vol. 37, No. 24, August 20, 1998.
	C2	Jean-Francois Lepage, et al., "Apodizing holographic gratings for the modal control of semiconductor lasers", Applied Optics, Vol. 36, No. 21, July 20, 1997.
	C3	Carlow R. Fernandez-Pousa, et al., "Talbot conditions, Talbot resonators, and first-order systems", J. Opt. Soc. AM. A, Vol. 20, No. 4, April 2003.
	C4	R.G. Waarts, et al. "Coherent Radiation from a broad area semiconductor laser in an external cavity", Laser-Diode Technology and Applications II, SPIE, Vol. 1219, (1990).
	C5	Sylvan Mailhot, et al. "Single-mode operation of a broad-area semiconductor laser with an anamorphic external cavity: experimental and numerical results" Applied Optics, Vol 39, No. 36, December 20, 2000.
	C6	Morris B. Snipes, Jr., et al. "Transverse mode filtering of wide stripe semiconductor lasers using an external cavity", SPIE Vol, 1634, Laser Diode Technology and Applications IV (1992).
	C7	A.C. Fey-den Boer, et al.. "Grating feedback in a 810 nm broad-area diode laser", Applied Physics, B. 63, 117-120 (1996).
	C8	Sylvie Yiou, et al. "Improvement of the spatial beam quality of laser sources with an intracavity Bragg grating", Optics Letters, Vol. 28, No. 4, February 15, 2003.
	C9	W. Nagengast, et al., "High-power single-mode emission from a broad-area semiconductor laser with a pseudoexternal cavity and a Fabry-Perot etalon", Optics Letters, Vol. 22, No. 16, August 15, 1997.
	C10	Damien Stryckman, et al., "Improvement of the lateral-mode discrimination of broad-area diode lasers with a profiled reflectivity output facet", Applied Optics, Vol. 35, No. 30, October 20, 1996.
	C11	Takashige Omatsu, et al. "Longitudinal-single mode operation of broad-stripe laser diode using a photorefractive phase conjugator", SPIE, Vol. 2896 (1996)

EXAMINER	DATE CONSIDERED
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant(s).	